Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

WHAT IS CLAIMED IS:

1. (Currently Amended) A dielectric device having a dielectric film formed directly or indirectly on at least a part of a glass substrate or a plastic substrate, said dielectric film comprising a) silicon oxide in a part at least in the direction of the film thickness, and formed at a temperature between about 90°C and less than 200°C, the composition ratio of silicon and oxygen being between 1:1.941 and 1:21.98 both inclusive, or b) silicon nitride in a part at least in the direction of the film thickness, and formed at a temperature between about 90°C and less than 200°C, the composition ratio of silicon and nitrogen being between 3:3.84 and 3:4 both inclusive.

2. (Currently Amended) A dielectric device having a dielectric film formed directly or indirectly on at least a part of a glass substrate or a plastic substrate, said dielectric film comprising a) silicon nitride in a part at least in the direction of the film thickness, and formed in a plasma environment having an electron density of at least $3x10^{11}cm^{-3}$, the composition ratio of silicon and nitrogen being between 3:3.84 and 3:4 both inclusive, or b) silicon oxide in a part at least in the direction of the film thickness, and formed in a plasma environment having an electron density of at least $3x10^{11}cm^{-3}$, the composition ratio of silicon and oxygen being between 1:1.94 and 1:2 both inclusive.

3. (Currently Amended) A dielectric device having a dielectric film formed directly or indirectly on at least a part of a glass substrate or a plastic substrate, said dielectric film comprising silicon oxynitride ~~having silicon oxide~~ in which the composition ratio of silicon and oxygen is between 1:1.941 and 1:21.98 both inclusive in a part at least in the direction of the film thickness, or the composition ratio of ~~said dielectric film comprising silicon oxynitride having silicon nitride in which the composition ratio of~~ silicon and nitrogen is between 3:3.84 and 3:4 both inclusive in a part at least in

the direction of the film thickness, and the film is formed in a plasma environment having an electron density of at least $3x10^{11}cm^{-3}$.

4. (Previously Presented) A dielectric device according to any one of claims 1 through 3, wherein a silicon layer or a silicon compound layer is formed directly or indirectly on at least a part of said glass substrate or said plastic substrate, and wherein said dielectric film is formed on at least a part of said silicon layer or said silicon compound layer.

5. (Previously Presented) A dielectric device according to any one of claims 1 through 3, wherein said plastic substrate is made of polyimide resin, polyetherketone resin, polyethersulfone resin, polyetherimide resin, polyethylenenaphthalate resin or polyester resin.

6. (Canceled) .

7. (Canceled) .

8. (Canceled) .

9. (Canceled) .

10. (Canceled) .

11. (Canceled) .

12. (Canceled) .

13. (Currently Amended) A semiconductor device having a dielectric film formed on at least a part of a silicon layer formed directly or indirectly on at least a part of a glass substrate or a plastic substrate, said dielectric film comprising a) silicon oxide in which the composition ratio of silicon and oxygen is between 1:1.9~~4~~1 and 1:2~~1.98~~ both inclusive ~~in a part at least in the direction of the film thickness~~ and which is formed at a temperature between about 90°C and less than 200°C, or b) silicon nitride in a part at least in the direction of the film thickness, and formed at a temperature between about

90°C and less than 200°C, the composition ratio of silicon and nitrogen being between 3:3.84 and 3:4 both inclusive.

14. (Currently Amended) A semiconductor device having a dielectric film formed on at least a part of a silicon layer formed directly or indirectly on at least a part of a glass substrate or a plastic substrate, said dielectric film comprising a) silicon nitride in which the composition ratio of silicon and nitrogen is between 3:3.84 and 3:4 both inclusive, ~~in a part at least in the direction of the film thickness~~ and which is formed in a plasma environment having an electron density of at least $3x10^{11}cm^{-3}$, or b) silicon oxide in which the composition ratio of silicon and oxygen is between 1:1.94 and 1:2 both inclusive, and which is formed in a plasma environment having an electron density of at least $3x10^{11}cm^{-3}$.

15. (Currently Amended) A semiconductor device having a dielectric film formed on at least a part of a silicon layer formed directly or indirectly on at least a part of a glass substrate or a plastic substrate, said dielectric film ~~comprising~~ being silicon oxynitride in which ~~having silicon oxide in which~~ the composition ratio of silicon and oxygen is between 1:1.9~~41~~ and 1:2~~1.98~~ both inclusive, or the composition ~~in a part at least in the direction of the film thickness, or said dielectric film comprising silicon oxynitride having silicon nitride in which the composition~~ ratio of silicon and nitrogen is between 3:3.84 and 3:4 both inclusive, and which is formed in a plasma environment having an electron density of at least $3x10^{11}cm^{-3}$. ~~in a part at least in the direction of the film thickness.~~

16. (Previously Presented) A semiconductor device according to any one of claims 13 through 15, wherein said dielectric film constitutes a part of a gate dielectric layer relative to the direction of the thickness of the gate dielectric layer.

17. (Original) A semiconductor device according to any one of claims 13 through 15, wherein said plastic substrate is made of polyimide resin, polyetheretherketone resin, polyethersulfone resin, polyetherimide resin, polyethylenenaphthalate resin or polyester resin.

18. (Canceled)

19. (Canceled)

20. (Canceled)

21. (Canceled)

22. (Canceled)

23. (Canceled)

24. (Canceled)

25. (Canceled)

26. (New) A dielectric device having a dielectric film formed directly or indirectly on at least a part of a glass substrate or a plastic substrate, said dielectric film comprising silicon oxynitride in which the composition ratio of silicon and oxygen is between 1:1.94 and 1:2 both inclusive in a part at least in the direction of the film thickness, or the composition ratio of silicon and nitrogen is between 3:3.84 and 3:4 both inclusive in a part at least in the direction of the film thickness, and the film is formed at a temperature between about 90°C and less than 200°C.